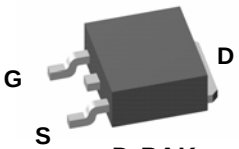
ON Semiconductor®

FDD8444-F085

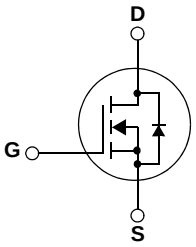
N-Channel PowerTrench® MOSFET
40V, 50A, 5.2mΩ

Features

- Typ $R_{DS(on)}$ = 4mΩ at V_{GS} = 10V, I_D = 50A
- Typ $Q_{g(10)}$ = 89nC at V_{GS} = 10V, I_D = 50A
- Low Miller Charge
- Low Qrr Body Diode
- UIS Capability (Single Pulse/ Repetitive
- RoHS Compliant
- Qualified to AEC Q101



D-PAK
(TO-252)



Applications

- Automotive Engine Control
- Powertrain Management
- Solenoid and Motor Drivers
- Electronic Transmission
- Distributed Power Architecture and VRMs
- Primary Switch for 12V Systems

MOSFET Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DSS}	Drain to Source Voltage	40	V
V_{GS}	Gate to Source Voltage	±20	V
I_D	Drain Current Continuous (V_{GS} = 10V)	50	A
	Pulsed	Figure 4	
E_{AS}	Single Pulse Avalanche Energy (Note 1)	535	mJ
P_D	Power Dissipation	153	W
	Derate above 25°C	1.02	W/°C
T_J, T_{STG}	Operating and Storage Temperature	-55 to +175	°C
$R_{\theta JC}$	Thermal Resistance Junction to Case	0.98	°C/W
$R_{\theta JA}$	Thermal Resistance Junction to Ambient, 1in^2 copper pad area	52	°C/W

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDD8444	FDD8444-F085	TO-252AA	13”	12mm	2500 units

Notes:
1: Starting T_J = 25°C, L = 0.67mH, I_{AS} = 40A
2: A suffix as “…F085P” has been temporarily introduced in order to manage a double source strategy as ON Semiconductor has officially announced in August 2014.

September-2017,Rev.2

Publication Order Number:
FDD8444-F085/D

Electrical Characteristics T_A = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
B_{VDSS}	Drain to Source Breakdown Voltage	I_D = 250μA, V_{GS} = 0V	40	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 32V, V_{GS} = 0V	-	-	1	μA
		V_{DS} = 32V, V_{GS} = 0V, T_A = 150°C	-	-	250	μA
I_{GSS}	Gate to Source Leakage Current	V_{GS} = ±20V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{GS} = V_{DS}, I_D = 250μA	2	2.5	4	V
$r_{DS(on)}$	Drain to Source On Resistance	I_D = 50A, V_{GS}= 10V	-	4	5.2	mΩ
		I_D = 50A, V_{GS}= 10V, T_J = 175°C	-	7.2	9.4	mΩ
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 25V, V_{GS} = 0V, f = 1MHz	-	6195	-	pF
C_{oss}	Output Capacitance		-	585	-	pF
C_{rss}	Reverse Transfer Capacitance		-	332	-	pF
R_G	Gate Resistance	f = 1MHz	-	1.9	-	Ω
$Q_{g(TOT)}$	Total Gate Charge at 10V	V_{GS} = 0 to 10V, V_{DD} = 20V, I_D = 50A	-	89	116	nC
$Q_{g(TH)}$	Threshold Gate Charge	V_{GS} = 0 to 2V, V_{DD} = 20V, I_D = 50A		11	-	nC
Q_{gs}	Gate to Source Gate Charge	V_{DD} = 20V, I_D = 50A	-	23	-	nC
Q_{gd}	Gate to Drain “Miller“ Charge	V_{DD} = 20V, I_D = 50A	-	20	-	nC

Switching Characteristics

t_{on}	Turn-On Time	V_{DD} = 20V, I_D = 50A, V_{GS} = 10V, R_{GS} = 2Ω	-	-	135	ns
$t_{d(on)}$	Turn-On Delay Time		-	12	-	ns
t_r	Rise Time		-	78	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	48	-	ns
t_f	Fall Time		-	15	-	ns
t_{off}	Turn-Off Time		-	-	95	ns

Drain-Source Diode Characteristics

V_{SD}	Source to Drain Diode Voltage	I_{SD} = 50A	-	-	1.25	V
		I_{SD} = 25A	-	-	1.0	V
t_{rr}	Reverse Recovery Time	I_{SD} = 50A, dI_{SD}/dt = 100A/μs	-	39	51	ns
Q_{rr}	Reverse Recovery Charge		-	45	59	nC

Typical Characteristics

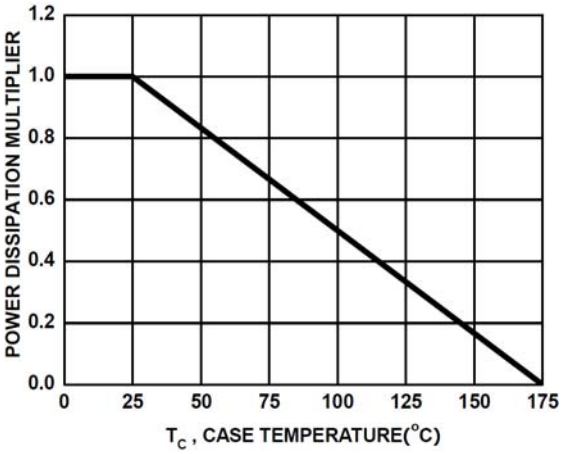


Figure 1. Normalized Power Dissipation vs Case Temperature

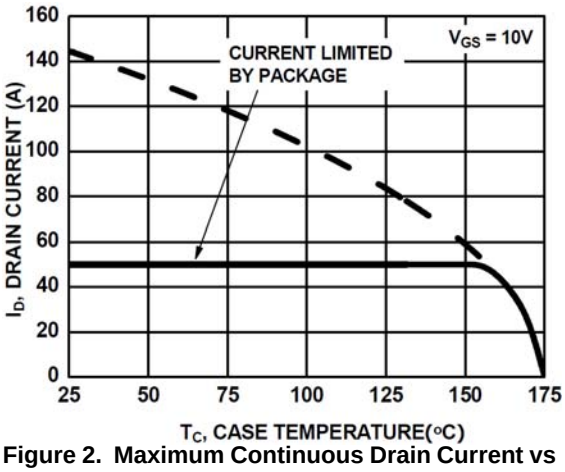


Figure 2. Maximum Continuous Drain Current vs Case Temperature

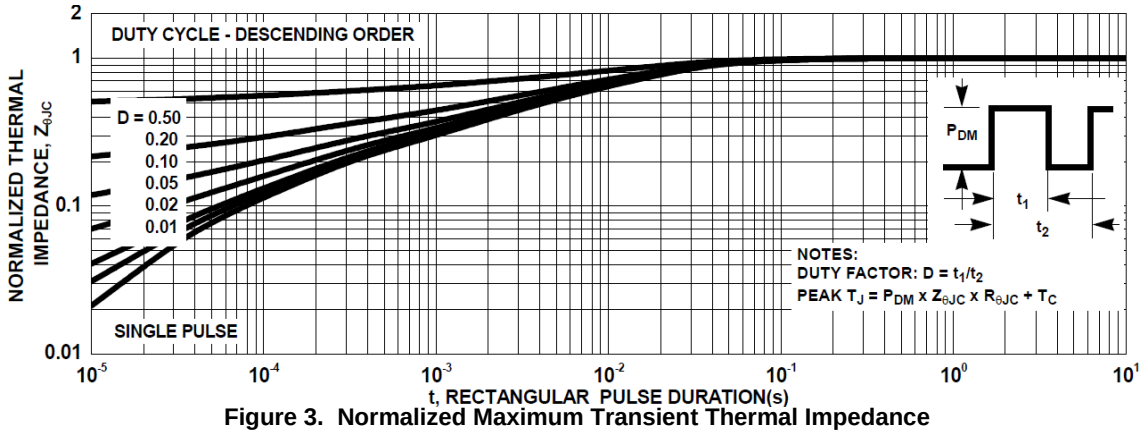


Figure 3. Normalized Maximum Transient Thermal Impedance

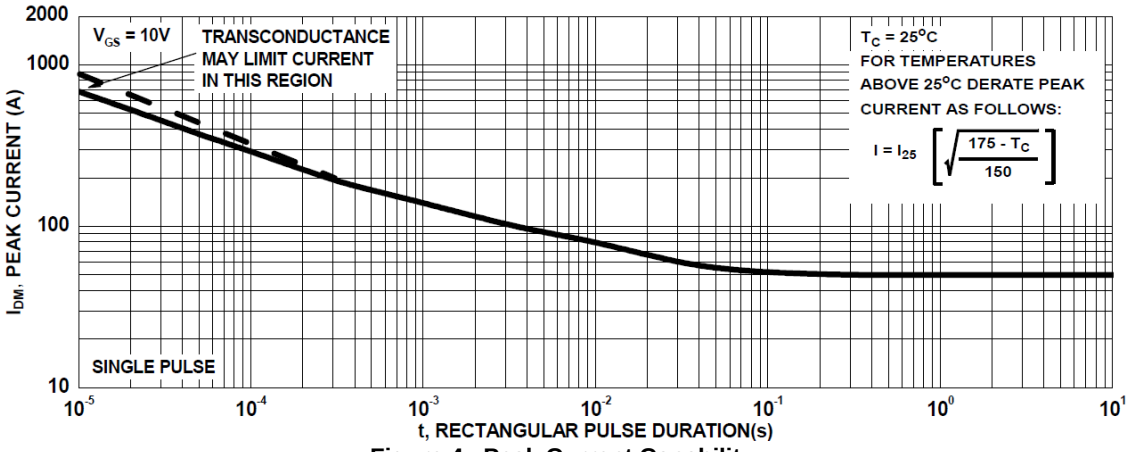


Figure 4. Peak Current Capability

Typical Characteristics

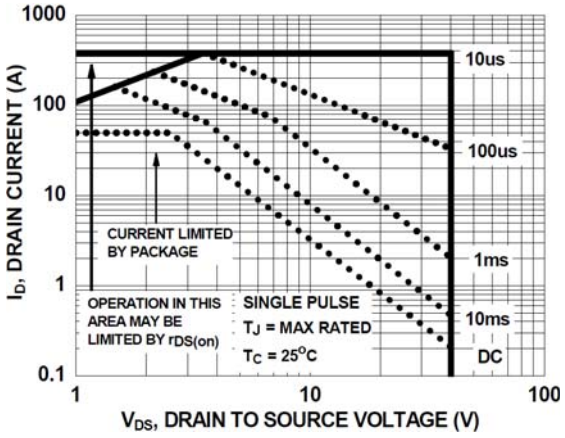
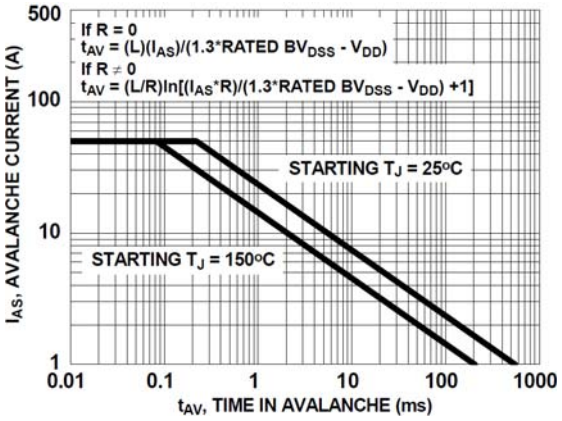


Figure 5. Forward Bias Safe Operating Area



NOTE: Refer to ON Semiconductor Application Notes AN7514 and AN7515

Figure 6. Unclamped Inductive Switching Capability

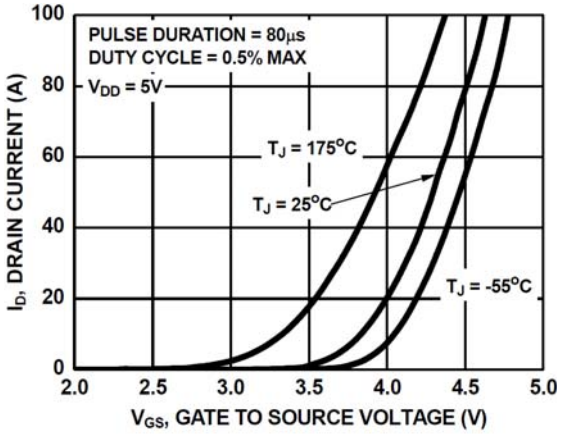


Figure 7. Transfer Characteristics

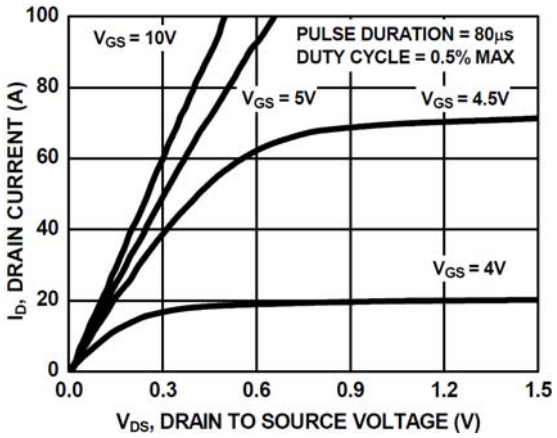


Figure 8. Saturation Characteristics

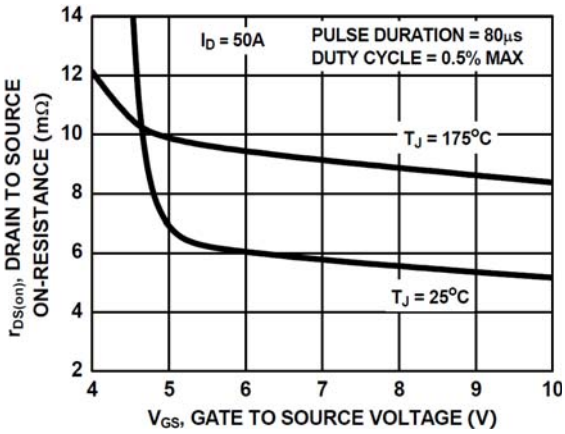


Figure 9. Drain to Source On-Resistance Variation vs Gate to Source Voltage

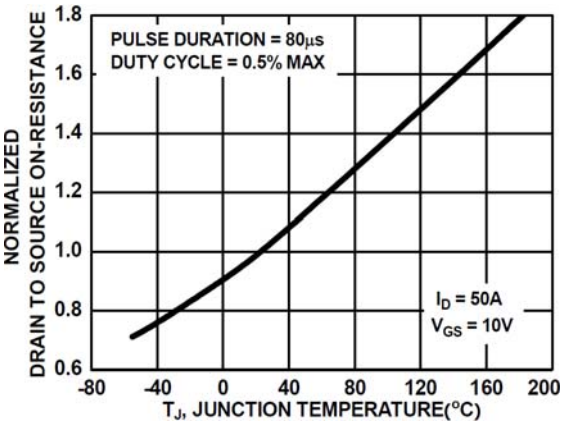


Figure 10. Normalized Drain to Source On Resistance vs Junction Temperature

Typical Characteristics

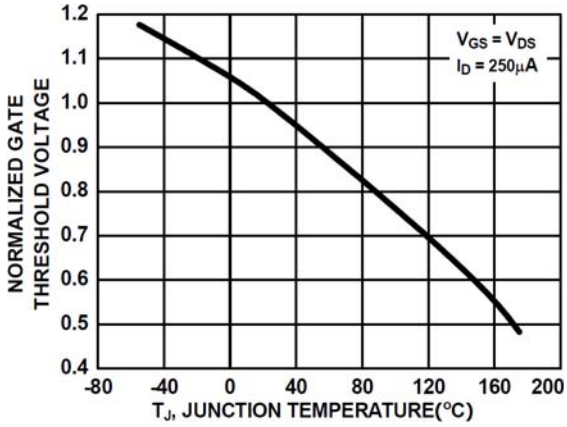


Figure 11. Normalized Gate Threshold Voltage vs Junction Temperature

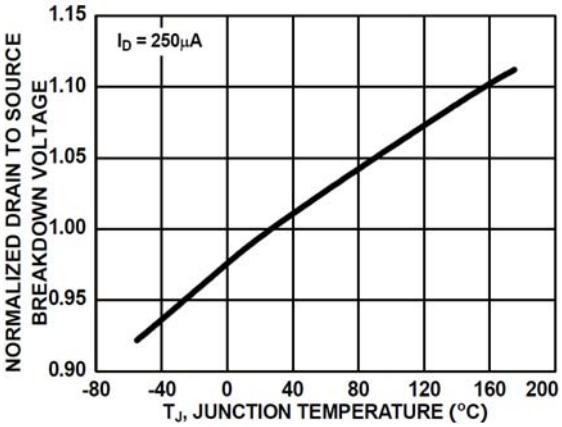


Figure 12. Normalized Drain to Source Breakdown Voltage vs Junction Temperature

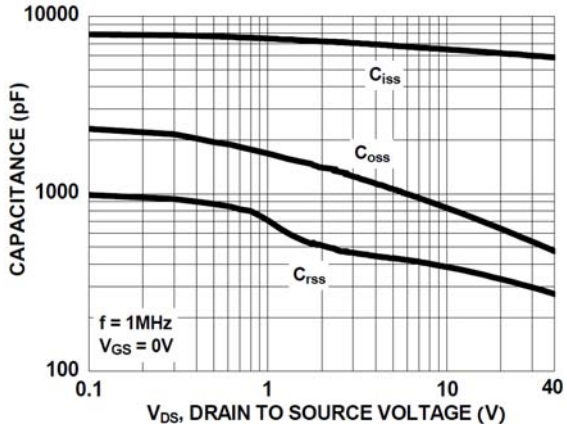


Figure 13. Capacitance vs Drain to Source Voltage

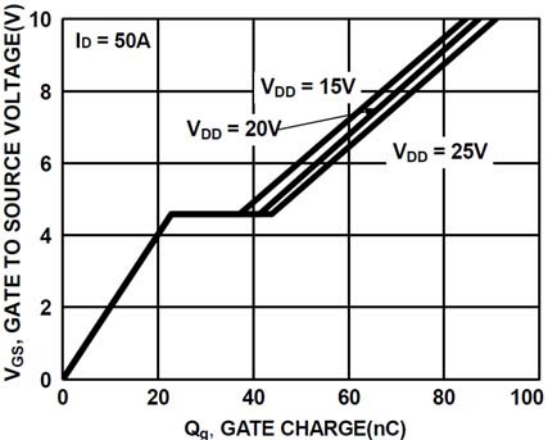


Figure 14. Gate Charge vs Gate to Source Voltage

PUBLICATION ORDERING INFORMATION

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